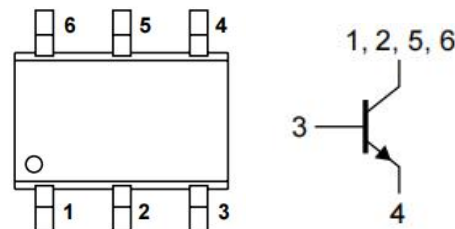


**SOT-23-6L Bipolar Transistor 双极型三极管**

■ **Features 特点**

NPN Low Saturation Voltage 低饱和压降

■ **Absolute Maximum Ratings 最大额定值**



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	$V_{CBO}$	60	V
Collector-Emitter Voltage 集电极发射极电压	$V_{CEO}$	50	V
Emitter-Base Voltage 发射极基极电压	$V_{EBO}$	6	V
Collector Current 集电极电流	$I_C$	3000	mA
Peak Collector Current 峰值集电极电流	$I_{CM}$	5000	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-65to+150 $^\circ\text{C}$	

■ **Device Marking 产品打标**

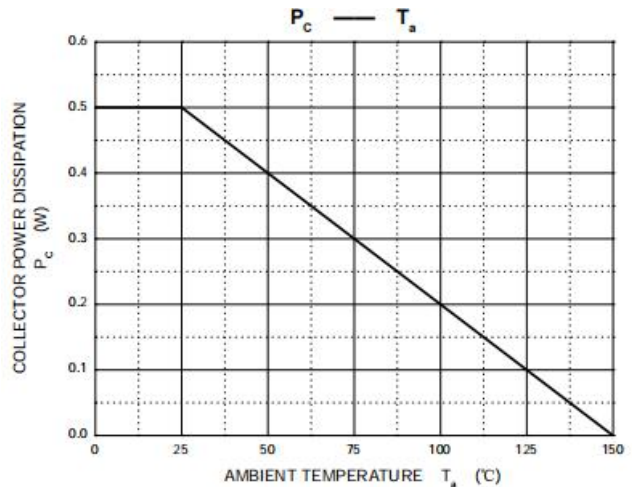
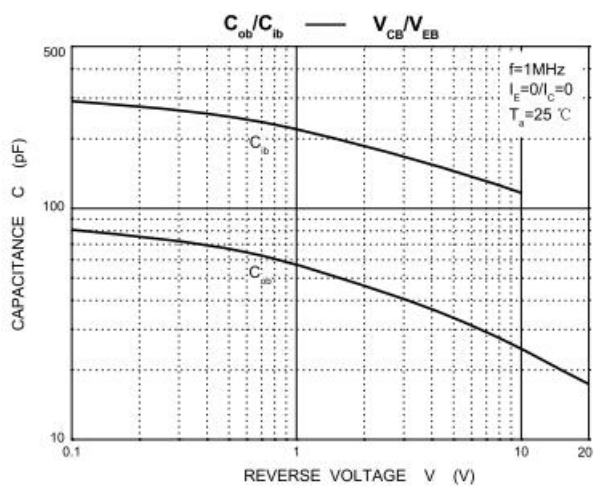
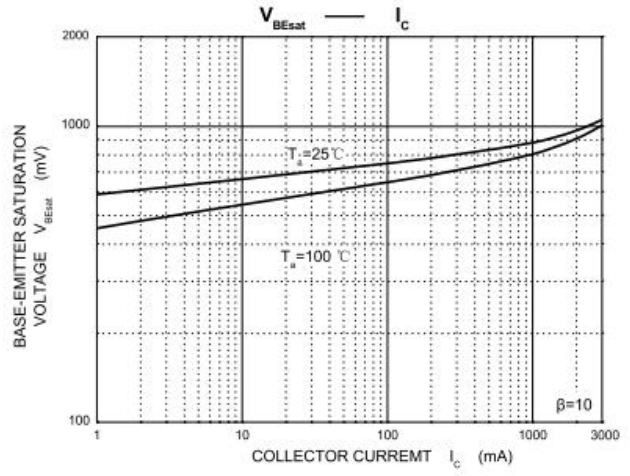
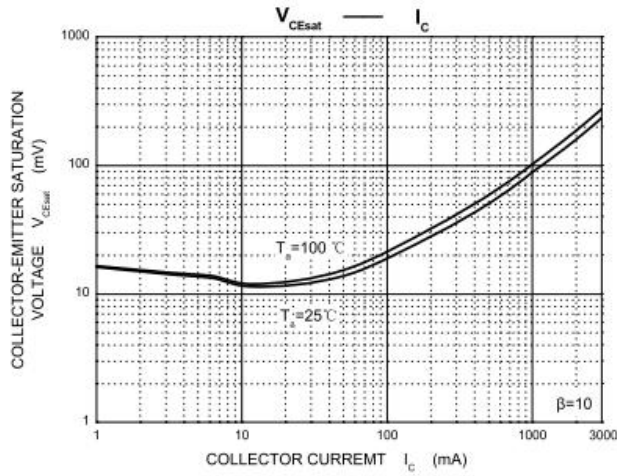
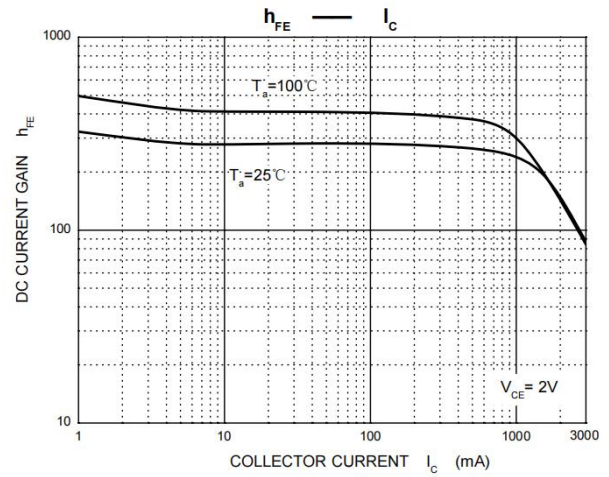
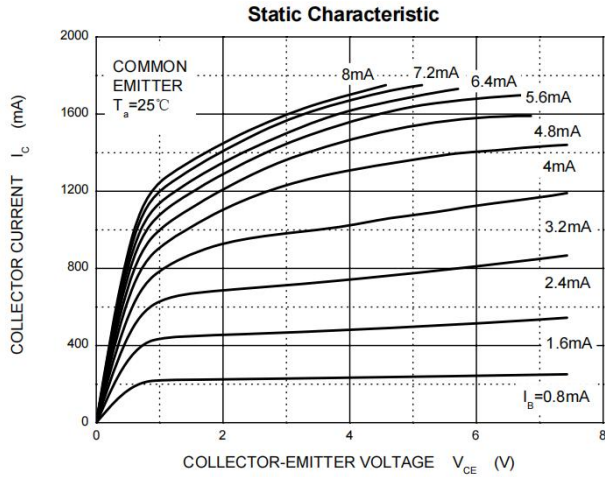
TYPE	BSS4350D
Marking	43

■ Electrical Characteristics 电特性

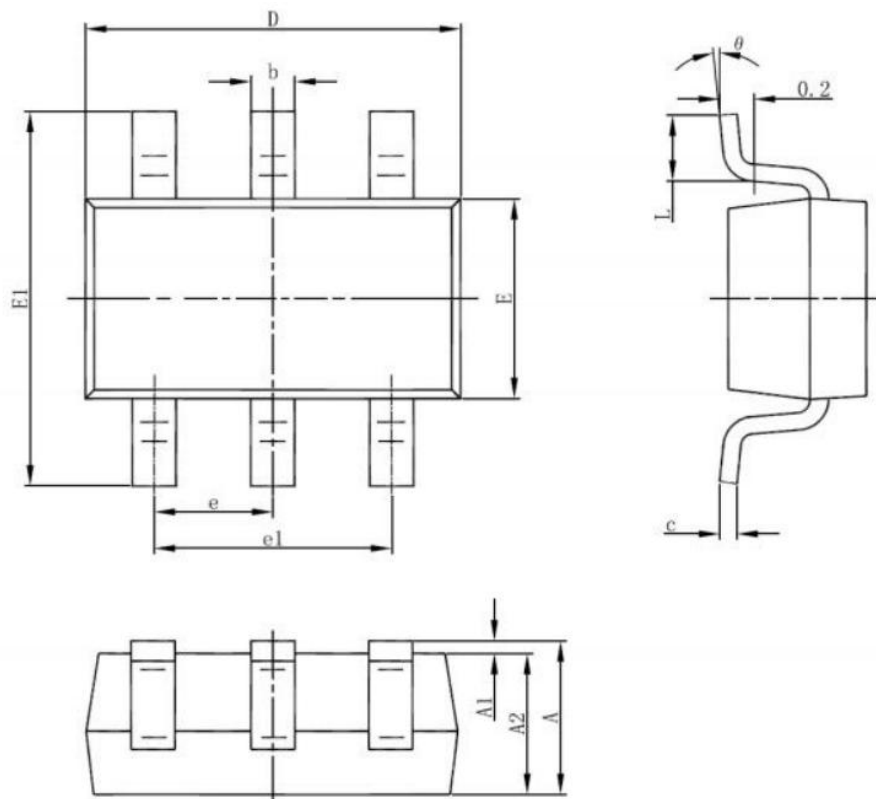
(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(I <sub>C</sub> = 100μA, I <sub>E</sub> =0)	BV <sub>CBO</sub>	60	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(I <sub>C</sub> = 10mA, I <sub>B</sub> =0)	BV <sub>CEO</sub>	50	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(I <sub>E</sub> = 100μA, I <sub>C</sub> =0)	BV <sub>EBO</sub>	6	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V <sub>CB</sub> = 50V, I <sub>E</sub> =0)	I <sub>CBO</sub>	—	—	100	nA
Emitter-Base Leakage Current 发射极基极漏电流(V <sub>EB</sub> = 5V, I <sub>C</sub> =0)	I <sub>EBO</sub>	—	—	100	nA
DC Current Gain(V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA) 直流电流增益(V <sub>CE</sub> = 2V, I <sub>C</sub> = 1000mA) (V <sub>CE</sub> = 2V, I <sub>C</sub> = 2000mA)	H <sub>FE</sub>	200 200 100	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA) (I <sub>C</sub> = 1000mA, I <sub>B</sub> = 50mA) (I <sub>C</sub> = 2000mA, I <sub>B</sub> = 200mA)	V <sub>CE(sat)</sub>	—	—	90 170 290	mV
Base-Emitter Saturation Voltage 基极发射极饱和压降(I <sub>C</sub> = 2000mA, I <sub>B</sub> = 200mA)	V <sub>BE(sat)</sub>	—	—	1.2	V
Transition Frequency 特征频率(V <sub>CE</sub> = 5V, I <sub>C</sub> = 100mA)	f <sub>T</sub>	100	—	—	MHz
Output Capacitance 输出电容(V <sub>CB</sub> = 10V, I <sub>E</sub> =0, f=1MHz)	C <sub>ob</sub>	—	—	30	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°